

T-51-21

MM54HC14/MM74HC14



# MM54HC14/MM74HC14 Hex Inverting Schmitt Trigger

## General Description

The MM54HC14/MM74HC14 utilizes advanced silicon-gate CMOS technology to achieve the low power dissipation and high noise immunity of standard CMOS, as well as the capability to drive 10 LS-TTL loads.

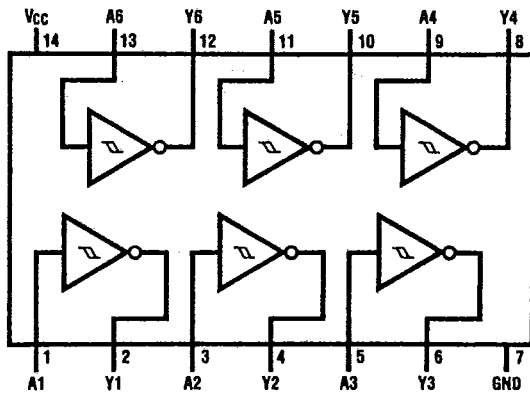
The 54HC/74HC logic family is functionally and pinout compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

## Features

- Typical propagation delay: 13 ns
- Wide power supply range: 2-6V
- Low quiescent current: 20  $\mu$ A maximum (74HC Series)
- Low input current: 1  $\mu$ A maximum
- Fanout of 10 LS-TTL loads
- Typical hysteresis voltage: 0.9V at  $V_{CC}=4.5V$

## Connection and Schematic Diagrams

Dual-In-Line Package

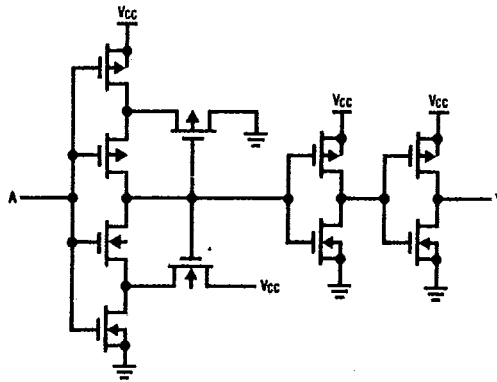


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Top View

Order Number MM54HC14\* or MM74HC14\*

\*Please look into Section 8, Appendix D for availability of various package types.



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**Absolute Maximum Ratings** (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V <sub>CC</sub> )	-0.5 to +7.0V
DC Input Voltage (V <sub>IN</sub> )	-1.5 to V <sub>CC</sub> +1.5V
DC Output Voltage (V <sub>OUT</sub> )	-0.5 to V <sub>CC</sub> +0.5V
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	±20 mA
DC Output Current, per pin (I <sub>OUT</sub> )	±25 mA
DC V <sub>CC</sub> or GND Current, per pin (I <sub>CC</sub> )	±50 mA
Storage Temperature Range (T <sub>STG</sub> )	-65°C to +150°C

Power Dissipation (P <sub>D</sub> )	600 mW
(Note 3)	
S.O. Package only	500 mW
Lead Temp. (T <sub>L</sub> ) (Soldering 10 seconds)	260°C

**Operating Conditions**

	Min	Max	Units
Supply Voltage (V <sub>CC</sub> )	2	6	V
DC Input or Output Voltage (V <sub>IN</sub> , V <sub>OUT</sub> )	0	V <sub>CC</sub>	V
Operating Temp. Range (T <sub>A</sub> )			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C

**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	V <sub>CC</sub>	T <sub>A</sub> = 25°C		74HC	54HC	Units
				Typ		T <sub>A</sub> = -40 to 85°C	T <sub>A</sub> = -55 to 125°C	
V <sub>T+</sub>	Positive Going Threshold Voltage	Minimum	2.0V	1.2	1.0	1.0	1.0	V
			4.5V	2.7	2.0	2.0	2.0	V
			6.0V	3.2	3.0	3.0	3.0	V
		Maximum	2.0V	1.2	1.5	1.5	1.5	V
			4.5V	2.7	3.15	3.15	3.15	V
			6.0V	3.2	4.2	4.2	4.2	V
V <sub>T-</sub>	Negative Going Threshold Voltage	Minimum	2.0V	0.7	0.3	0.3	0.3	V
			4.5V	1.8	0.9	0.9	0.9	V
			6.0V	2.2	1.2	1.2	1.2	V
		Maximum	2.0V	0.7	1.0	1.0	1.0	V
			4.5V	1.8	2.2	2.2	2.2	V
			6.0V	2.2	3.0	3.0	3.0	V
V <sub>H</sub>	Hysteresis Voltage	Minimum	2.0V	0.5	0.2	0.2	0.2	V
			4.5V	0.9	0.4	0.4	0.4	V
			6.0V	1.0	0.5	0.5	0.5	V
		Maximum	2.0V	0.5	1.0	1.0	1.0	V
			4.5V	0.9	1.4	1.4	1.4	V
			6.0V	1.0	1.5	1.5	1.5	V
V <sub>OH</sub>	Minimum High Level Output Voltage	V <sub>IN</sub> = V <sub>IL</sub>  I <sub>OUT</sub>   = 20 μA	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V <sub>IN</sub> = V <sub>IL</sub>  I <sub>OUT</sub>   = 4.0 mA  I <sub>OUT</sub>   = 5.2 mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V <sub>OL</sub>	Maximum Low Level Output Voltage	V <sub>IN</sub> = V <sub>IH</sub>  I <sub>OUT</sub>   = 20 μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V <sub>IN</sub> = V <sub>IH</sub>  I <sub>OUT</sub>   = 4.0 mA  I <sub>OUT</sub>   = 5.2 mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I <sub>IN</sub>	Maximum Input Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	6.0V		±0.1	±1.0	±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND I <sub>OUT</sub> = 0 μA	6.0V		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V<sub>OH</sub> and V<sub>OL</sub>) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub> = 5.5V and 4.5V respectively. (The V<sub>IH</sub> value at 5.5V is 3.85V.) The worst case leakage current (I<sub>IN</sub>, I<sub>CC</sub>, and I<sub>OZ</sub>) occur for CMOS at the higher voltage and so the 6.0V values should be used.

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**AC Electrical Characteristics**  $V_{CC}=5V, T_A=25^{\circ}C, C_L=15 pF, t_r=t_f=6 ns$  **T-51-21**

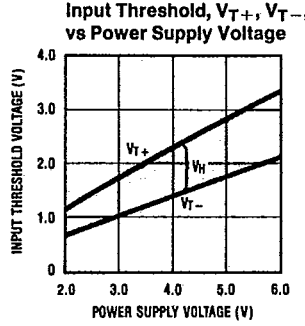
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay		12	22	ns

**AC Electrical Characteristics**  $V_{CC}=2.0V$  to  $6.0V, C_L=50 pF, t_r=t_f=6 ns$  (unless otherwise specified)

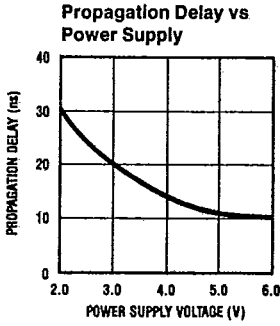
Symbol	Parameter	Conditions	$V_{CC}$	$T_A=25^{\circ}C$			Units	
				Guaranteed Limits				
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay		2.0V	60	125	156	ns	
			4.5V	13	25	31	ns	
			6.0V	11	21	26	ns	
$t_{TLH}, t_{THL}$	Maximum Output Rise and Fall Time		2.0V	30	75	95	ns	
			4.5V	8	15	19	ns	
			6.0V	7	13	16	ns	
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per gate)		27			pF	
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

**Typical Performance Characteristics**



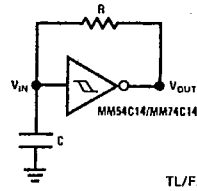
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TL/F/5105-4

**Typical Applications**

**Low Power Oscillator**



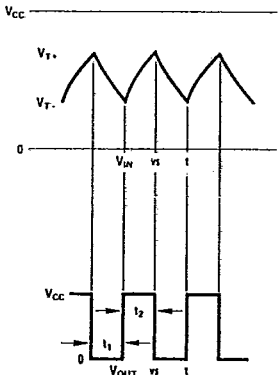
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$$t_1 \approx RC \ln \frac{V_{T+}}{V_{T-}}$$

$$t_2 \approx RC \ln \frac{V_{CC} - V_{T-}}{V_{CC} - V_{T+}}$$

$$f \approx \frac{1}{RC \ln \frac{V_{T+}(V_{CC} - V_{T-})}{V_{T-}(V_{CC} - V_{T+})}}$$

Note: The equations assume  $t_1 + t_2 \gg t_{p0} + t_{pd1}$



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